

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.



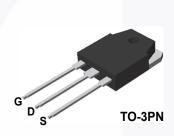
Features

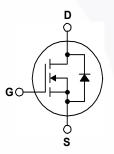
- 24 A, 500 V, $R_{DS(on)}$ = 200 m Ω (Max.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 90 nC)
- Low Crss (Typ. 55 pF)
- 100% Avalanche Tested
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQA24N50	Unit	
V _{DSS}	Drain-Source Voltage		500	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		24	A	
	- Continuous (T _C = 100°C)		15.2	A	
DM	Drain Current - Pulsed	(Note 1)	96	A	
V _{GSS}	Gate-Source Voltage		± 30		
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1100	mJ	
AR	Avalanche Current	(Note 1)	24	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	29	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns	
D	Power Dissipation ($T_C = 25^{\circ}C$)		290	W	
	- Derate above 25°C		2.33	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

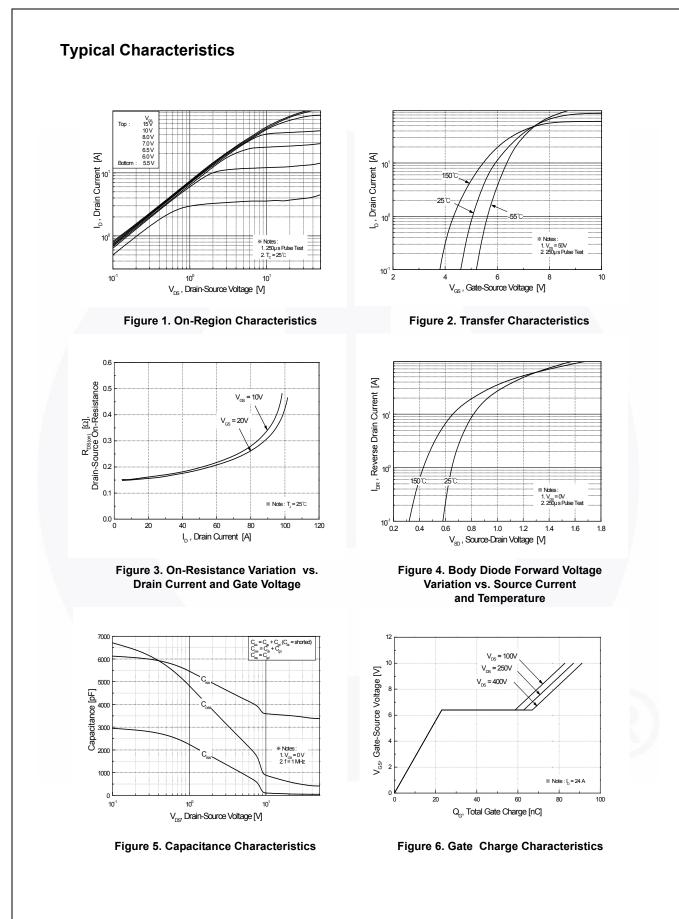
Thermal Characteristics

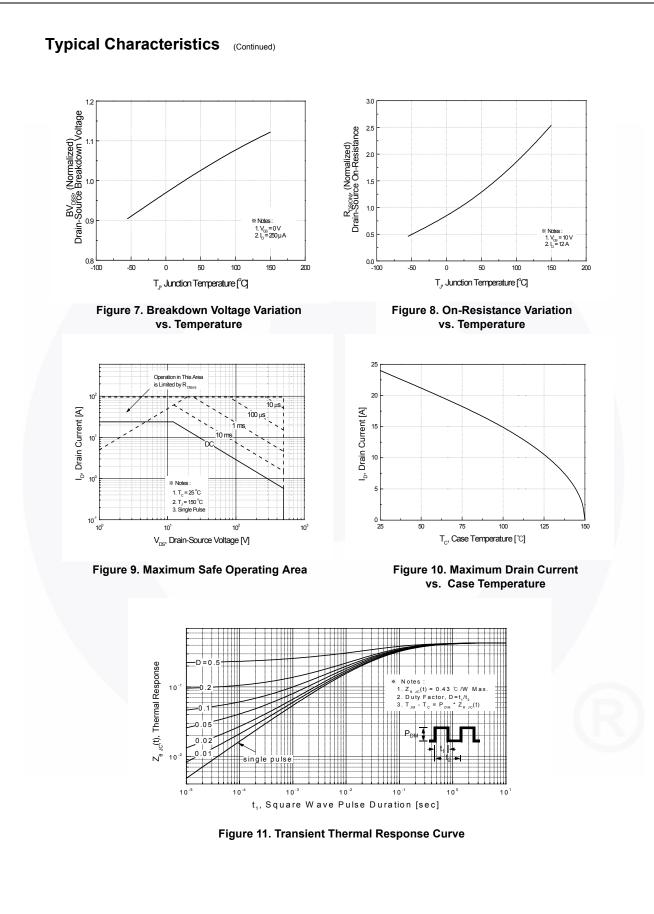
Symbol	Parameter	Тур.	Max.	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case		0.43	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24		°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient		40	°C/W	

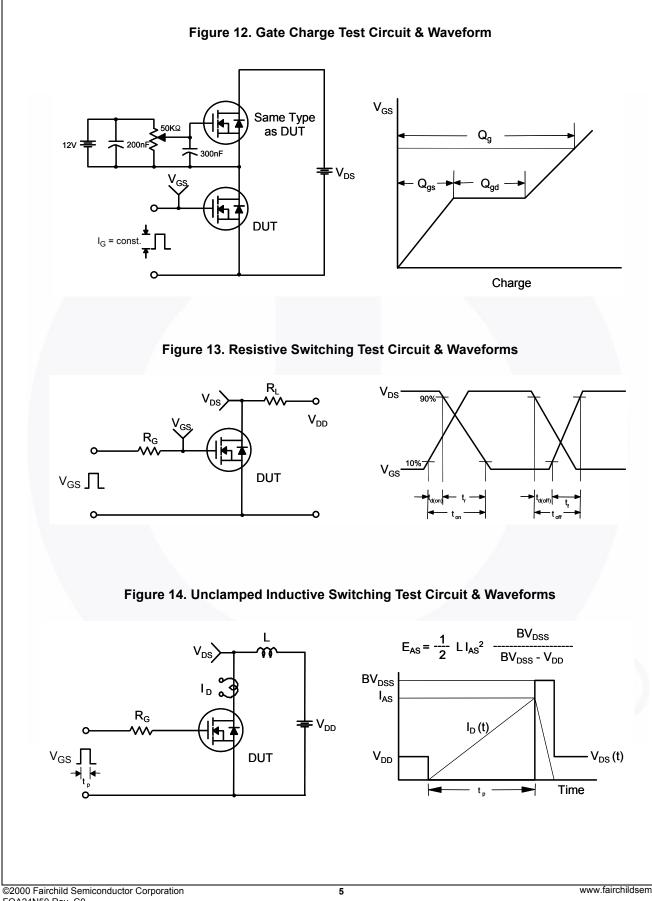
June 2014

П
Ø
\triangleright
Ñ
4
Ž
g
Ÿ
Ζ
Ī
$\overline{\mathbf{O}}$
い
n
E
ē
Ξ
<u>S</u>
- 11
Щ
٦
-
Š
0
S
Щ
-

•		Top Mark	Pack	Package Packing Method Reel Size		Tape Width		ı Qı	Quantity		
			-3PN Tube N/A		N/A			30 units			
Electric	al Char	acteristics $T_c =$	25°C un	less of	herwise note	ed.					
Symbol		Parameter	20 0 0			ondition	S	Min.	Тур.	Max.	Uni
Off Cha	rootoriotic			-							
BV _{DSS}	aracteristics Drain-Source Breakdown Voltage		V _{GS} = 0 V, I _D = 250 μA			500			V		
$\Delta BV_{DSS}/$	Breakdown Voltage Temperature Coeffi-					000					
ΔT_{J}	cient			$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$					0.53		V/°C
I _{DSS}	Zero Gate Voltage Drain Current			V _{DS} = 500 V, V _{GS} = 0 V						1	μA
			$V_{DS} = 400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$						10	μA	
I _{GSSF}	Gate-Body Leakage Current, Forward			V _{GS} = 30 V, V _{DS} = 0 V						100	nA
I _{GSSR}	Gate-Body	Leakage Current, Rev	erse	V _{GS}	= -30 V, V _D s	_s = 0 V				-100	nA
On Cha	racteristic	s									
V _{GS(th)}	Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 25$				250 µA		3.0		5.0	V	
R _{DS(on)}	Static Drain On-Resista	n-Source			= 10 V, I _D =				0.156	0.2	Ω
9 _{FS}	Forward Tr	ansconductance		V _{DS}	= 50 V, I _D =	12 A			22		S
C _{iss}	c Charact			V _{DS}	= 25 V, V _{GS}	= 0 V,			3500	4500	pF
C _{oss}	Output Ca	pacitance		f = 1	I.0 MHz		-		520	670	pF
C _{rss}	Reverse T	ransfer Capacitance							55	70	pF
Switchi	ng Charao	teristics									
t _{d(on)}	Turn-On D					04.4			80	170	ns
t _r	Turn-On R	ise Time			$V_{DD} = 250 \text{ V}, \text{ I}_{D} = 24 \text{ A},$ R _G = 25 Ω		-		250	500	ns
t _{d(off)}	Turn-Off D	elay Time		'`G	20 32		F		200	400	ns
t _f	Turn-Off Fa	all Time		(Note 4)		(Note 4)		155	320	ns	
Qg	Total Gate	Charge		VDS	= 400 V, I _D :	= 24 A,			90	120	nC
Q _{gs}	Gate-Sour	ce Charge			5		-		23		nC
Q _{gd}	Gate-Drain	Charge		(Note 4)		(Note 4)		44		nC	
Q _{gs} Q _{gd}				V _{GS} = 10 V (Note 4)			(Note 4)				
	1	de Characteristic				ngs				0.1	
l _S	Maximum Continuous Drain-Source Diode Forward Current								24	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current							96	A		
V _{SD}		ce Diode Forward Volta	age	$V_{GS} = 0 V, I_S = 24 A$						1.4	V
t _{rr}		ecovery Time		$V_{GS} = 0 V, I_S = 24 A,$		-		400		ns	
Q _{rr}	Reverse R	ecovery Charge		alF	/ dt = 100 A/µ	15			4.3		μC







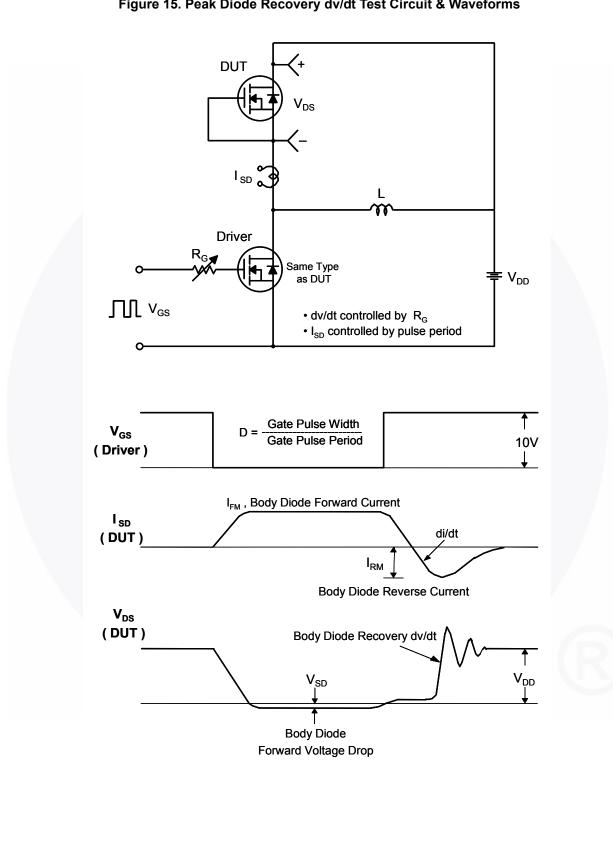
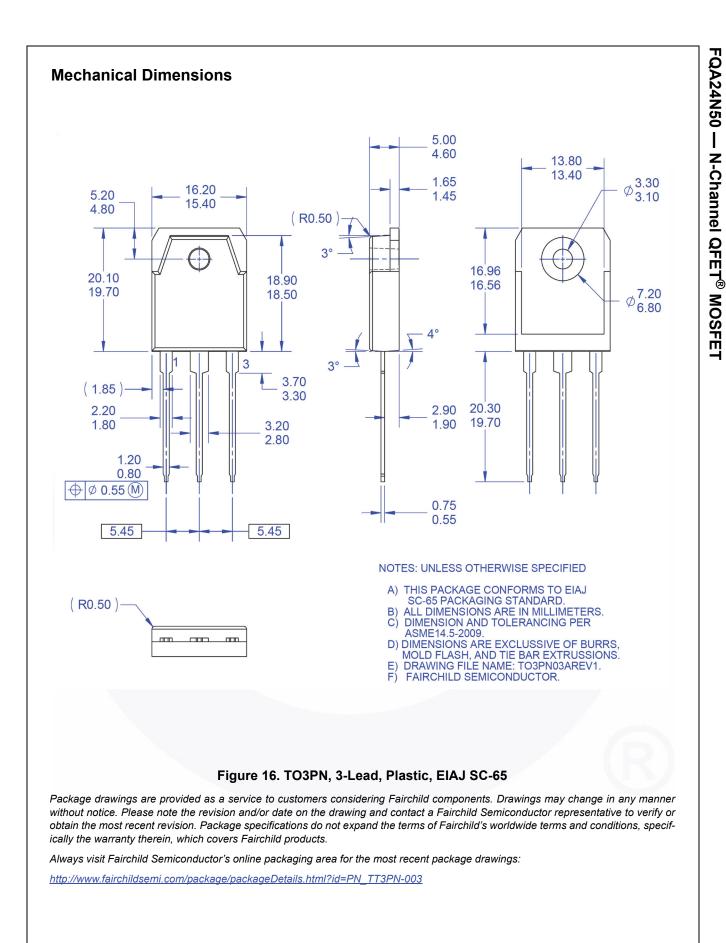


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: FQA24N50